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Team Nexperia

25 June 2013 Product data sheet

## 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in DFN1006-2 (SOD882) leadless ultra small Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

Average forward current: I<sub>F(AV)</sub> ≤ 200 mA

Reverse voltage: V<sub>R</sub> ≤ 30 V

Low forward voltage: V<sub>F</sub> ≤ 450 mV
Low reverse current: I<sub>R</sub> ≤ 0.5 μA

AEC-Q101 qualified

Leadless ultra small SMD plastic package

## 3. Applications

- Low current rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; f = 20 kHz; T <sub>amb</sub> ≤ 115 °C; square wave	[1]	-	-	200	mA
		$\delta$ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 135 °C; square wave		-	-	200	mA
V <sub>R</sub>	reverse voltage			-	-	30	V
V <sub>F</sub>	forward voltage	$I_F$ = 10 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C; pulsed		-	330	450	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C		-	0.14	0.5	μΑ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.





200 mA low VF MEGA Schottky barrier rectifier

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		1 - 2
2	А	anode		sym001
			Transparent top view	
			DFN1006-2 (SOD882)	

<sup>[1]</sup> The marking bar indicates the cathode.

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
RB520CS3002L	DFN1006-2	leadless ultra small plastic package; 2 terminals	SOD882			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
RB520CS3002L	ZA

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage			-	30	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; f = 20 kHz; $T_{amb} \le$ 115 °C; square wave	[1]	-	200	mA
		$\delta$ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 135 °C; square wave		-	200	mA
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; half sine wave		-	3	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	315	mW
			[1]	-	565	mW
			[3]	-	865	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uig-a)	thermal resistance	in free air	[1][2]	-	-	395	K/W
	from junction to		[1][3]	-	-	220	K/W
	ambient		[1][4]	-	-	145	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	70	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.

RB520CS3002L

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#### 200 mA low VF MEGA Schottky barrier rectifier

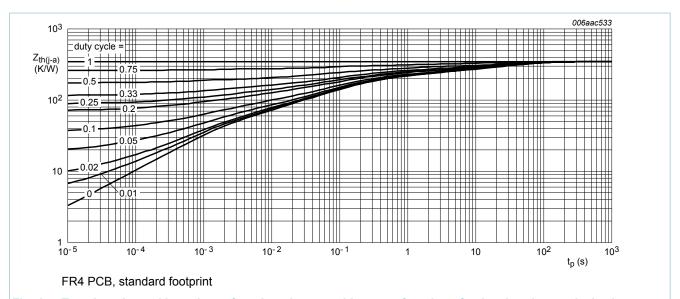


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

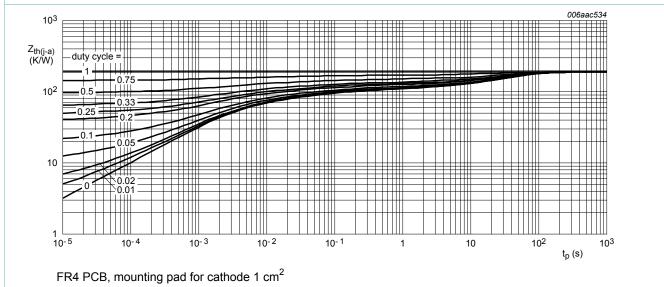
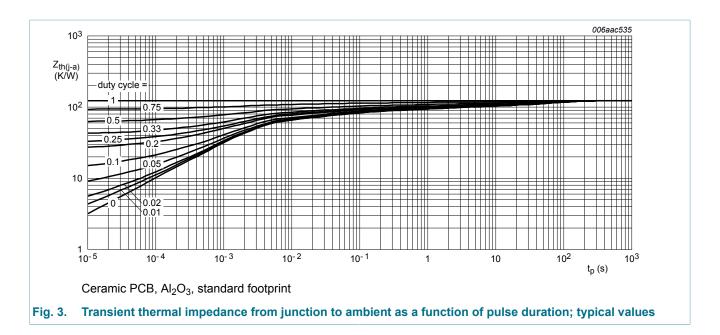


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

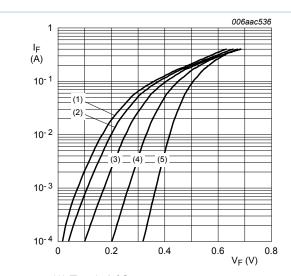
### 200 mA low VF MEGA Schottky barrier rectifier



## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	$I_F$ = 0.1 mA; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_j$ = 25 °C; pulsed	-	210	-	mV
		$I_F$ = 1 mA; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_j$ = 25 °C; pulsed	-	270	-	mV
		$I_F$ = 10 mA; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_j$ = 25 °C; pulsed	-	330	450	mV
		$I_F$ = 100 mA; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_j$ = 25 °C; pulsed	-	450	-	mV
		$I_F$ = 200 mA; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_j$ = 25 °C; pulsed	-	540	640	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C	-	0.14	0.5	μA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	10	-	pF



(1) 
$$T_j = 150 \, ^{\circ}C$$

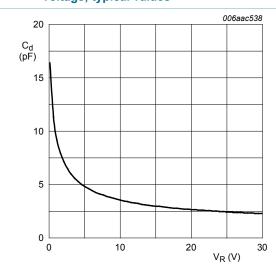
(2) 
$$T_i = 125 \, ^{\circ}C$$

(3) 
$$T_i = 85 \, ^{\circ}C$$

(4) 
$$T_i = 25 \,^{\circ}C$$

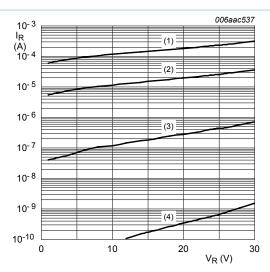
(5) 
$$T_j = -40 \, ^{\circ}\text{C}$$

Fig. 4. Forward current as a function of forward voltage; typical values



 $f = 1 MHz; T_{amb} = 25 °C$ 

Fig. 6. Diode capacitance as a function of reverse voltage; typical values



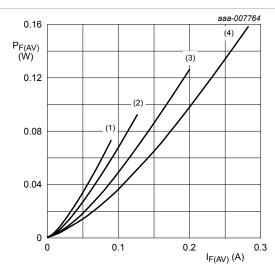
(1) 
$$T_i = 125 \, ^{\circ}C$$

(2) 
$$T_i = 85 \,^{\circ}C$$

(3) 
$$T_i = 25 \, ^{\circ}C$$

(4) 
$$T_i = -40 \, ^{\circ}C$$

Fig. 5. Reverse current as a function of reverse voltage; typical values



T<sub>i</sub> = 150 °C

(1) 
$$\delta$$
 = 0.1; f = 20 kHz

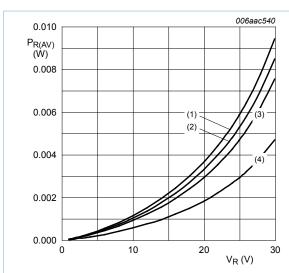
(2) 
$$\delta$$
 = 0.2; f = 20 kHz

(3) 
$$\delta$$
 = 0.5; f = 20 kHz

(4)  $\delta$  = 1; DC

Fig. 7. Average forward power dissipation as a function of average forward current; typical values

### 200 mA low VF MEGA Schottky barrier rectifier



T<sub>i</sub> = 125 °C

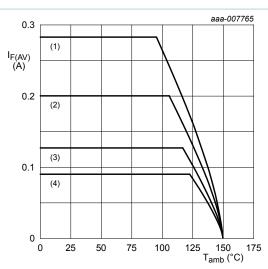
(1)  $\delta$  = 1; DC

(2)  $\delta$  = 0.9; f = 20 kHz

(3)  $\delta = 0.8$ ; f = 20 kHz

(4)  $\delta$  = 0.5; f = 20 kHz

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T<sub>i</sub> = 150 °C

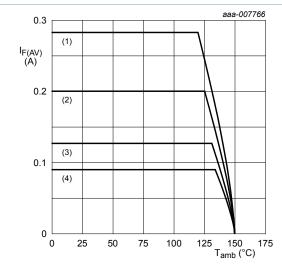
(1)  $\delta$  = 1; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

T<sub>i</sub> = 150 °C

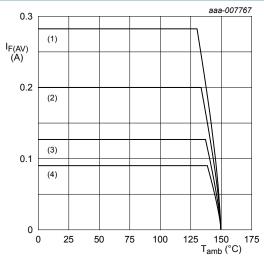
(1)  $\delta$  = 1; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

 $T_i = 150 \, ^{\circ}C$ 

(1)  $\delta$  = 1; DC

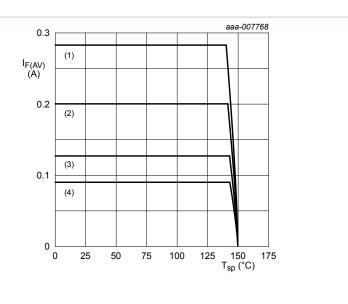
(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values

### 200 mA low VF MEGA Schottky barrier rectifier



 $T_i = 150 \, ^{\circ}C$ 

(1)  $\delta$  = 1; DC

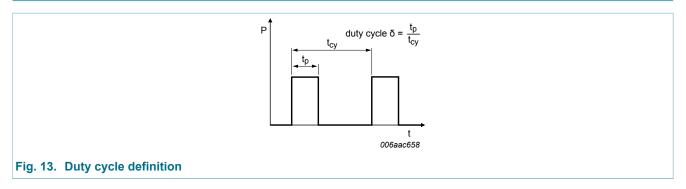
(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 12. Average forward current as a function of solder point temperature; typical values

### 11. Test information



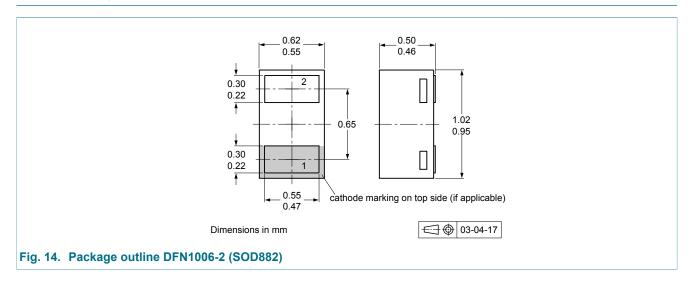
The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### 11.1 Quality information

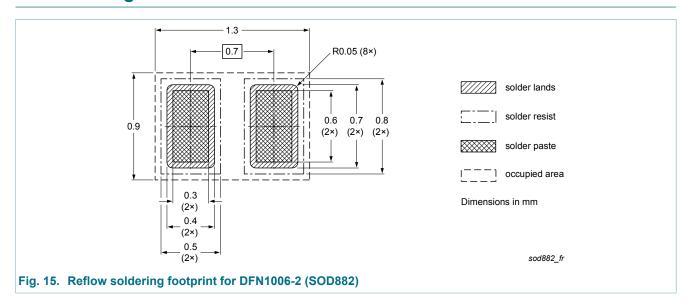
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

200 mA low VF MEGA Schottky barrier rectifier

## 12. Package outline



## 13. Soldering



**Product data sheet** 

200 mA low VF MEGA Schottky barrier rectifier

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
RB520CS3002L v.1	20130625	Product data sheet	-	-

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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